

# MA INTENANCE MANUAL 25—50 MHz RF ASSEMBLY 19D416478G1-G4, GI0-GI3

9. IMI

#### AND

## MIXER/IF BOARD 19C320094GI-G4

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## DESCRIPTION

The RF Assembly uses two tuned helical resonators and four L-C tuned circuits to provide front end selectivity.

The Mixer/IF board (MIF) uses the RF input from the RF Assembly and the mixer injection frequency from the oscillator/multiplier board to generate the IF frequency.

### CIRCUIT ANALYSIS

#### RF ASSEMBLY

#### ANTENNA INPUT A301A/A301B

An RF signal from the antenna is applied to A301 which provides an AC ground between vehicle ground and receiver A. Resistor R1 prevents a static charge from building up on the vehicle antenna. The output of A301 is coupled through two high-Q helical resonators (L301, C301 and L302, C302) to the RF amplifier. The coils are tuned to the incoming frequency by C301 and C302. Lamp DS1 protects the RF amplifier stage against an excessive RF input.

#### RF AMPLIFIER A302

RF Amplifier Ql is a Field-Effect Transistor (FET). Ql operates as a grounded gate amplifier, with the RF input applied

to the "source" terminal. This method of operation provides a low impedance input to the amplifier. The amplified output is taken from the "drain" terminal and coupled through four L-C tuned circuits (L1-C7, L2-C8, L3-C9 and L4-C10) to the mixer. The four tuned circuits and the two helical resonators provide the receiver front end selectivity.

#### MIXER-IF

#### MIXER & CRYSTAL FILTER

The mixer uses a FET (Q501) as the active device. The FET mixer provides a high input impedance, high power gain, and an output relatively free of harmonics (low in intermodulation products).

In the mixer stage, RF from the RF amplifier stage is coupled through tank circuit L501 and C502 to the gate of mixer Q501. The tank circuit provides increased selectivity and impedance matching between the RF Assembly and the gate of mixer Q501. Injection voltage from the multiplierselectivity stages is inductively coupled through L502 to the source of the mixer. The mixer IF output signal is coupled from the drain of Q501 through a tuned circuit (L504 and C511) which matches the mixer output to the input of the four-pole monolithic crystal filter. The highly-selective crystal filter (FL501 and FL502) provides the first portion of the receiver IF selectivity. The output of the filter is coupled

through impedance matching network Z502 (L520 and C523) to the IF amplifier.

#### IF AMPLIFIER

IF amplifier Q502 is a dual-gate FET. The filter output is applied to Gate 1 of the amplifier, and the output is taken from the drain. The biasing on Gate 2 and the drain load determines the gain of the stage. The amplifier provides approximately 20 dB of IF gain. The output of Q502 is coupled through a network (L521 and

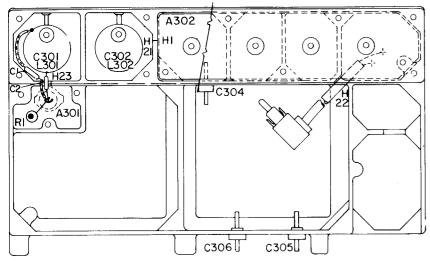
C528) that matches the amplifier output to the crystal filter on the next IF stage. The output of the MIF board is coupled to the next IF stage through feed-through capacitor C305.

Supply voltage for the RF amplifier and MIF board is supplied through feed-through capacitor C306. SERVICE NOTE: Variable capacitor C521 does not require adjustment when performing normal alignment. If the 4-pole monolithic crystal filter is replaced, then adjustment of C521 is necessary for optimum IF response.

GENERAL ELECTRIC COMPANY • MOBILE COMMUNICATIONS DIVISION WORLD HEADQUARTERS • LYNCHBURG, VIRGINIA 24502 U.S.A.



## RF ASSEMBLY BOTTOM VIEW



LEAD IDENTIFICATION FOR Q2



NOTE: LEAD ARRANGEMENT, AND NOT CASE SHAPE, IS DETERMINING FACTOR FOR LEAD IDENTIFICATION.

LEAD IDENTIFICATION FOR Q502

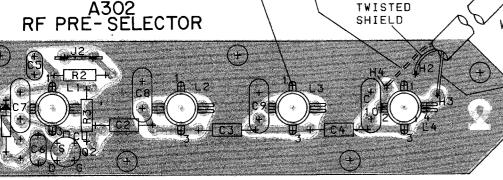


RAISED TAB ON COIL FORM INDICATES PIN 1 ON L1 - L4

IN H4 FOR GROUPS 1 THRU 4

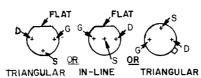
CENTER CONDUCTOR

A302 RF PRE- SELECTOR

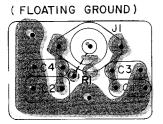


CENTER CONDUCTOR IN H3 FOR GROUPS 8 & 9

LEAD IDENTIFICATION (19C327759, Rev. 1) (19B219444, Sh. 1, Rev. 2) (19B219444, Sh. 2, Rev. 2)



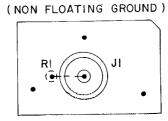
VIEW FROM CASE END NOTE: LEAD ARRANGEMENT, AND NOT CASE SHAPE, IS DETERMINING FACTOR FOR LEAD IDENTIFICATION.



A30IA ANT INPUT

(19B219449, Sh. 1, Rev. 2) (19B219449, Sh. 2, Rev. 2)

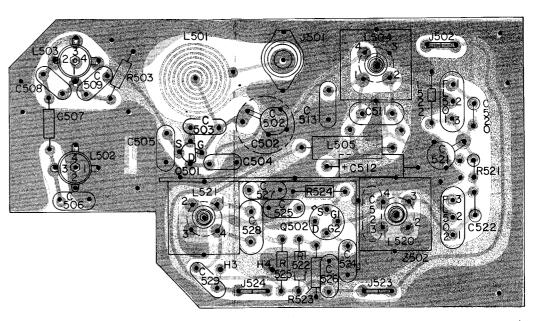
**A301B** ANT INPUT



(19D423628, Rev. 4)

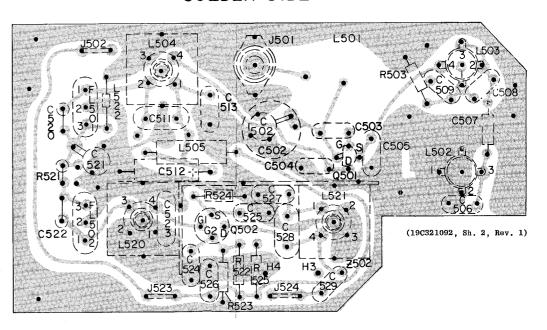
## M!XER/IF BOARD

## COMPONENT SIDE



(19C321092, Sh. 2, Rev. 1) (19C321092, Sh. 3, Rev. 1)

## SOLDER SIDE



RUNS ON SOLDER SIDE

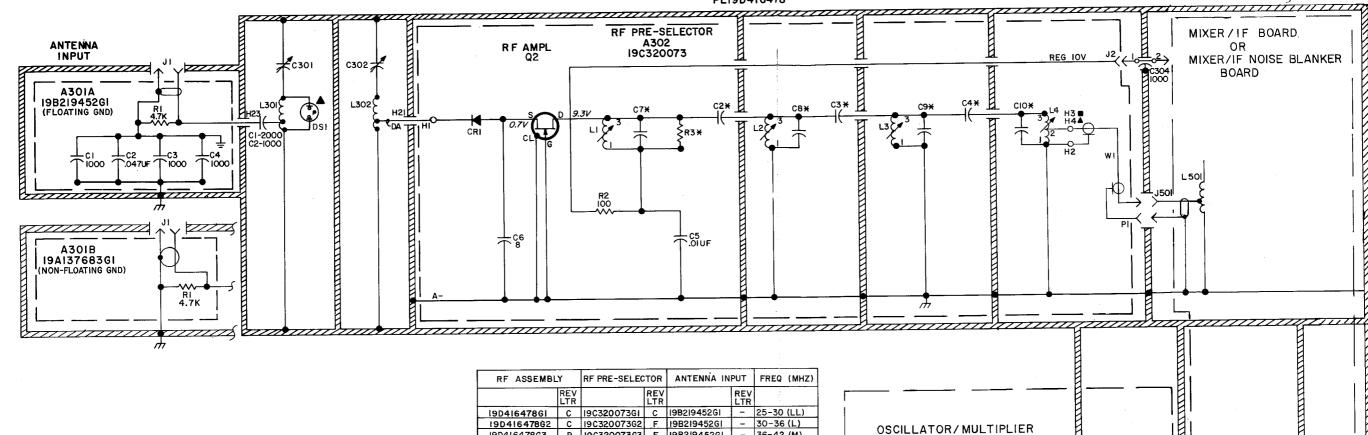
RUNS ON COMPONENT SIDE

## **OUTLINE DIAGRAM**

25-50 MHz RF ASSEMBLY AND MIXER/IF BOARD

Issue 4

#### R F ASSEMBLY PL19D416478



. >	COMPONE	NT VALUE T	ABLE	
COMP DESIG	LL	L	M'	H
RF FREQ	25-30 MHZ	30-36MHZ	36-42 MHZ	42-50 MHZ
IF FREQ	II.2 MHZ	9.4 M HZ	II.2 MHZ	9.4 MHZ
C2	1.0	.75	.68	.82
C3	1.0	.75	.68	.82
C4	1.0	.75	.68	.82
C7	51	39	301	18
C8	51	39	30	18
С9	51	39	30	18
CIO	56	39	30	18
R3			24K	.6.2 K

MID BAND					
* COMPONENT VALUE TABLE					
SPLIT	ML LOW	MH HIGH			
RF FREQ	66-78MHZ	77-88MHZ			
IF FREQ	11.2 MHZ	11.2 MHZ			
C 2	. 47	.39			
C3	.56	.47			
C4	1.0	-82			
* C7	15	10			
C8	18	13			
C9	18	13			
CIO	18	13			
R3	6.8K	6.8K			

RF ASSEMBL	Y	RF PRE-SELEC	TOR	ANTENNA IN	PLIT	FREQ (MHZ)
IN ACCEMIDE		III THE OLLLE		ARTERIOR III		11124 (11112)
	REV LTR		REV LTR		REV LTR	į.
19D416478GI	С	19C320073G1	C	19B219452GI	-	25-30 (LL)
19D416478G2	С	19C320073G2	F	19B219452GI	_	30-36 (L)
19D416478G3	В	19C320073G3	E	19B219452GI	-	36-42 (M)
I9D416478G4	В	19C320073G4	С	19B219452GI	-	42-50 (H)
19D416478G8	-	19C320073G8	-	19B219452G1	-	66-78 (ML)
19D416478G9	-	19C320073G9	-	198219452G1	-	77-88 (MH)
19D416478GIO	-	19C320073G1	,C	19B219452GI	-	25-30 (LL)
19D416478G11	7	19C320073G2	F	I9AI37683GI		30-36 (L)
J9D4I6478GI2	- )	19032007363	E	19A137683GI	<u> </u>	36-42 (M)
19D416478GI3	-	19C320073G4	C	19A137683GI	-	42-50 (H)
19D416478GI4	-	19032007368	-	19A137683GI	[ <del>-</del>	66-78 (ML)
19D4I6478GI5	-	19C320073G9	-	19A137683GI	-	77-88 (MH)

## VOLTAGE READINGS

VOLTAGE READINGS ARE TYPICAL READINGS MEASURED TO SYSTEM NEGATIVE (P903-10) WITH TEST SET MODEL 4EX3AII OR A 20,000 OHM-PER-VOLT METER.

- INDICATES A-
- ± INDICATES VEHICLE GROUND

ALL RESISTORS ARE 1/4 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY KEIDOO OHMS OR MEG = 1,000,000 OHMS CAPACITOR VALUES IN PICOFARADS (EQUAL TO MICROMICOFARADS, INDUCTANCE VALUES IN MICROHENRYS UNLESS FOLLOWED BY UF= MICROHENRYS UNLESS FOLLOWED BY MH= MILLIHENRYS OR H= HENRYS.

IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS. LIST FOR THAT PART.

## ▲ NOT PRESENT IN M.B. ■ NOT PRESENT IN L.B.

BOARD

## **SCHEMATIC DIAGRAM**

25-50 MHz RF ASSEMBLY

(19D423475, Rev. 10)

#### PARTS LIST

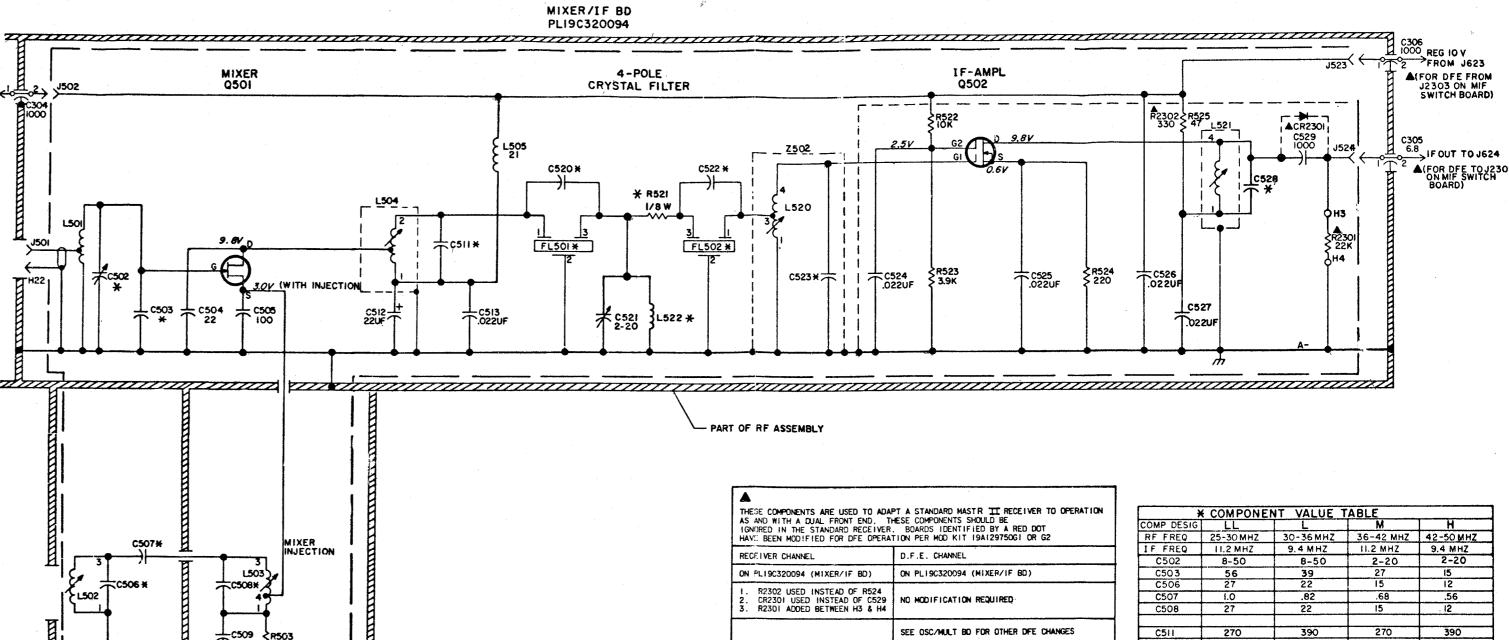
		LB14990E	C3L*	5491601P118	Phonolics 0.75 nd 15% 500 mey
		05.50.49	032	J451001F118	Phenolic: 0.75 pf ±5%, 500 VDCW.  In REV B & earlier:
	RF ASSE	25-50 MHz 19D416478G1-G4, G10-G13		5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.
	MI	AND F ASSEMBLY 19C320094G1-G4	C3W*	19A700013P11	Phenolic: 0.68 pf ±5%, 500 VDCW.
	7				In REV C & earlier;
SYMBOL	GE PART NO.	DESCRIPTION		5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.
		DESCRIPTION	С3Н*	19A700013P12	Phenolic: 0.82 pf ±5%, 500 VDCw.
					In REV A & earlier:
		RF ASSEMBLY 19D416478G1 25-30 MHz (LL) FLOATING GRD		5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCw.
	-	19D416478G2 30-36 MHz (L) FLOATING GRD 19D416478G3 36-42 MHz (M) FLOATING GRD	C4LL*	19A700013P13	Phenolic: 1.0 pf ±5%, 500 VDCW.
		19D416478G4 42-50 MHz (H) FLOATING GRD 19D416478G10 25-30 MHz (LL) NON FLOATING GRD	1		In REV A & earlier;
1		19D416478G11 30-36 MHz (L) NON FLOATING GRD 19D416478G12 36-42 MHz (M) NON FLOATING GRD		5491601P122	Phenolic: 1.2 pf ±5%, 500 VDCW.
1		19D416478G13 42-50 MHz (H) NON FLOATING GRD	C41*	5491601P118	Phenolic; 0.75 pf ±5%, 500 VDCW.
A301A		COMPONENT BOARD			In REV B & earlier:
ĺ		19B219452G1		5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.
			C4M*	19A700013P11	Phenolic: 0.68 pf ±5%, 500 VDCw.
Cl	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.			In REV C & earlier:
C2	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.		5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.
С3	19Al16655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to	C4H*	19A700013P12	Phenolic: 0.82 pf ±5%, 500 VDCw.
and C4		RMC Type JF Discap.			In REV A & earlier:
		JACKS AND RECEPTACLES		5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.
J1	19A130924G1	Connector, receptacle: coaxial, jack type; sim	C5 C6	19A116080P101	Polyester: 0.01 µf ±10%, 50 VDCW.
		to Cinch 14H11613.	C7LL	19A116656P8K8 5496219P256	Ceramic: 8 pf ±1 pf ±10%, ~80 PPM.  Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef
			0,22	0.302231230	-80 PPM.
Rl	19A700106P79	Composition: 4.7% ohms ±5%, 1/4 w.	C7L	5496219P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef -80 PPM.
			C7M	5496219P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef
A301B		ANTENNA PLATE ASSEMBLY 19A137683G1	0.711	540.00707045	-80 РРМ.
			С7н	5496219P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.
Jl	7104941P20	JACKS AND RECEPTACLES	CSLL	5496219P256	Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef -80 PPM,
01	7104041220	Connector, jack: sim to National Tel.	CSL	5496219P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef
		RESISTORS			-80 РРМ.
RI	19A700106P79	Composition: 4.7K ohms ±5%, 1/4 w.	C8M	5496219P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.
A302		COMPONENT BOARD 19C320073G1 25-30 MHz (LL)	С8Н	5496219P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.
		19C320073G2 30-36 MHz (L) 19C320073G3 36-42 MHz (M)	C914L	5496219P256	Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef -80 PPM.
		19C320073G4 42-50 MHz (H)	Car	5496219P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef
1					-80 РРМ.
C3™*	19A700013P13	Phenolic: 1.0 pf ±5%, 500 VDCW.	C9M	5496219P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.
	5491601P122	In REV A & earlier: Phenolic: 1.2 pf ±5%, 500 VDCW.	С9Н	5496219P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.
C2L*	5491601P118	Phenolic: 0.75 pf ±5%, 500 VDCW.	CIOFF	5496219P257	Ceramic disc: 56 pf ±5%, 500 VDCW, temp coef
		In REV B & earlier:	CIOL	5496219P253	-80 PPM.
	5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.	CTOL	54962197255	Ceramic disc: 39 pf $\pm 5\%$ , 500 VDCW, temp coef $-80$ PPM.
C2 <b>M</b> *	19A700013P11	Phenolic: 0.68 pf ±5%, 500 VDCW.	CIOM	5496219P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef ~80 PPM.
		In REV C & earlier:	С10Н	5496219P245	Ceramic disc: 18 pf ±5%, 500 VDCw, temp coef
	5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.			-80 PPM.
C2H*	19A700013P12	Phenolic: 0.82 pf ±5%, 500 VDCW.			
	J	In REV A & earlier:	CR1	19A116052P2	Silicon, hot carrier: Fwd. drop .410 volts max.
	5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.			
C3TT*	19A700013P13	Phenolic: 1.0 pf ±5%, 500 VDCW.	70	10411205***	JACKS AND RECEPTACLES
		In REV A & earlier:	J2	19A116975Pl	Receptacle, wire spring.
	5491601P122	Phenolic: 1.2 pf ±5%, 500 VDCW.			
		<b>]</b>			
	Ì				
	NITE ADDED DELL	ETED OR CHANGED BY PRODUCTION CHANGES			

SYMBOL

GE PART NO.

DESCRIPTION

\*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES



VOLTAGE	READINGS
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VOLTAGE READINGS ARE TYPICAL READINGS MEASURED TO SYSTEM NEGATIVE (P903-10) WITH TEST SET MODEL 4EX3AII OR A 20,000 OHM-PER-VOLT METER.

INDICATES A-

INDICATES VEHICLE GROUND

ALL REI OTHERV VALUES K=1000 CAPACIT TO MICE IN MICR

	MIXER/IF BD			
RESISTORS ARE 1/4 WATT UNLESS	19032009461	D	25-30 (LL)	11.2
RWISE &PECIFIED AND RESISTOR ES IN OHMS UNLESS FOLLOWED BY DO OHMS OR MES *1,000,000 OHMS * CITOR VALUES *4 PICOFARADS (EQUAL	190320094G2	D	30-36 (L)	9,4
	19032009463	С	36-42 (M)	11.2
	19C32O094G4	С	42-50 (H)	9.4
ICROMICROFARADS) UNLESS FOLLOWED  * MICROFARADS. INDUCTANCE VALUES  CONTROL OF THE STREET OF THE STR				
MILLIHENRYS OR H&HENRYS				

THESE ITEMS ARE SUPPLIED IN MOD. KIT PLIPA129750GI.

THESE ITEMS ARE SUPPLIED IN MOD. KIT PL19A129750G2.

REV FREQ

LETTER RANGE (MHZ) FREQ (MHZ)

(19D423476, Rev. 2)

IN	OR	DER	TO	RETAI	N R	ATED	EQUIP	MEN
PE	RFO	RMA	NCE.	REP	LAC	EME	NT OF	AN
SE	RVIC	E F	ART	SHOULD	BE	MADE	ONL	( With
A	CON	PON	ENT	HAVING	THE	SPE	CIFICA	ATION
SH	OWN	ON	THÈ	PARTS	LIST	FOR	THAT	PART

IT PALL	] 11.2 MITZ	3.4 MITZ	1 11.2 191112	3.4 (0.172
C502	8-50	8-50	2-20	2-20
C5Q3	56	39	27	15
C506	27	22	15	12
C507	1.0	.82	.68	.56
C508	27	22	15	. 12
			}	
C511	270	390	270	390
	<u> </u>			ļ
	<u> </u>			
C520	.47	.68	.47	.68
		<u> </u>	<u> </u>	<u> </u>
C522	.47	.68	.47	.68
C523	91	100	91	100
55 Maria			<u> </u>	
C528	330	360	330	360
L522	15	18	15	18
R521	560	330	560	330
FL50I	FL50ILL	FL50IL	FL50IM	FL50IH
FL502	FL502LL	FL502L	FL502M	FL502H

## SCHEMATIC DIAGRAM

25—50 MHz MIXER/IF BOARD

Issue 3

LBI4989

## LBI4989

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
ļ									311111111	UL FART NO.	DESCRIPTION
			L301M	19B219455G3	Coil. Includes:	C508LL	19A116656P27K8	Ceramic disc: 27 pf ±10%, 500 VDCW, temp coef -80 PPM.			
L1* thru L3*	19C307170P306	Coil, RF: variable; sim to Paul Smith 092574-DS-3.	C2	5494481P11	Capacitor, ceramic disc: 1000 pf ±20%, 1000 VDCw; sim to RMC Type JF Discap.	C508L	19A116656P24K8	Ceramic disc: 24 pf ±10%, 500 VDCW, temp coef	J501	19A130924G1	Receptacle, coaxial; jack type; sim to Cinch 14H11613.
		In 19C320073G1 REV A & earlier: In 19C320073G2 REV B & earlier;	C301	19B209159P4	Capacitor, variable, air: 1.80 to 8.3 pf, 650 v peak; sim to EF Johnson 189.	C508M	19A116656P15K8	-80 PPM.  Ceramic disc: 15 pf ±10%, 500 VDCW, temp coef	J502	19A116975P1	Receptacle, wire spring.
		In 19C320073G3 REV C & earlier: In 19C320073G4 REV A & earlier:	D <b>S</b> 1	19B209067Pl	Lamp, glow: 0.7 ma; sim to GE NE2ET.			-80 PPM.	J523 and	19A116975P1	Receptacle, wire spring.
	19B219419G2	Coil. Includes:	T301H	19B219455G3	Coil. Includes:	C508H	19A116656P12K8	Ceramic disc: 12 pf ±10%, 500 VDCW, temp coef -80 PPM.	J524		
14*	5491798P5	Tuning slug.	C2	5494481P11	Capacitor, ceramic disc: 1000 pf ±20%, 1000 VDCw; sim to RMC Type JF Discap.	C509	19A116080P101	Polyester: 0.01 µf ±10%, 50 VDCW.	1501		(Part of printed board 19C321092P1).
IA.	19C307170P308	Coil, RF: variable; sim to Paul Smith 071774-0G-7. In 19C320073G1 REV A & earlier:	C301	19B209159P4	Capacitor, variable, air: 1.80 to 8.3 pf, 650 v peak; sim to EF Johnson 189.	C511	5490008P137	Silver mica: 270 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.	L502	19B219419G2	Coil. Includes:
		In 19C320073G2 REV B & earlier: In 19C320073G3 REV C & earlier:	DS1	19B209067P1	Lamp, glow: 0.7 ma; sim to GE NE2ET.	C511L	5490008P141	Silver mica: 390 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.		5491798P5	Tuning slug.
	19B219419G1	In 19C320073G4 REV A & earlier; Coil. Includes:	L302LL	19B219455G2	Coil. Includes:	C511M	5490008P137	Silver mica: 270 pf ±10%, 500 VDCw; sim to	1.503	19B219419G4	Coil. Includes:
	5491798P5	Tuning slug.	C302	19B209159P4	Capacitor, variable, air: 1.80 to 8.3 pf, 650 v peak; sim to EF Johnson 189.	or law	E4000000143	Electro Motive Type DM-15.	1,504	5491798P5	Tuning slug.
		PLUGS	L302L	19B219455G2	Coil. Includes:	C511H	5490008Pl41	Silver mica: 390 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.	L504	19C320141G30 5493185P12	Coil. Includes; Tuning slug.
Pl		(Part of W1).	C302	19B209159P4	Capacitor, variable, air: 1.80 to 8.3 pf, 650 v peak; sim to EF Johnson 189.	C512	5496267P10	Tantalum: 22 $\mu$ f $\pm 20\%$ , 15 VDCW; sim to Sprague Type 150D.	L505	7488079P48	Choke, RF: 27.0 µh ±10%, 1.40 ohms DC res max;
Q1* ~	19A116154P1	N Type, field effect. Deleted in Gl & G4 by REV C.	L302M	19B219455G4	Coil. Includes:	C513	19A116080P3	Polyester: 0.022 µf ±20%, 50 VDCW.	L520LL		sim to Jeffers 4422-9K. (Part of 2502LL).
		Deleted in G2 & G3 by REV E.	C302	19B209159P4	Capacitor, variable, air: 1.80 to 8.3 pf, 650 v peak; sim to EF Johnson 189.	С520LL	19A700013P9	Phenolic: 0.47 pf ±5%, 500 VDCW.	L520L	·	(Part of 2502LL).
Q2*	19A116960P1	N Type, field effect; sim to Type 2N4416. Added to G1 & G4 by REV C. Added to G2 & G3 by REV E.	1302Н	19B219455G4	Coil. Includes:	C520L	19A700013P11	Phenolic: 0.68 pf ±5%, 500 VDCW.	L520M		(Part of 4502M).
			C302	19B209159P4	Capacitor, variable, air: 1.80 to 8.3 pf, 650 v	C520M C520H	19A700013P9 19A700013P11	Phenolic: 0.47 pf ±5%, 500 VDCW.  Phenolic: 0.68 pf ±5%, 500 VDCW.	1.520н		(Part of 4502H).
		RESISTORS			peak; sim to EF Johnson 189.	C521	19A700012P2	Variable: 2,5-20 pf, 200 VDCW, -250 to -700	L521	19C320141G6	Coil. Includes:
R2	19A700106P39	Composition: 100 ohms ±5%, 1/4 w.			MISCELLANEOUS	a=001;	10450001070	Parts/M/°C; sim to Panasonic ECV-12W20X32.		5493185P9	Tuning slug.
R3L*	3R152P303J	Composition: 30K ohms ±5%, 1/4 w. Deleted by REV B. Added to G2 by REV D. Deleted by REV F.		19B201074P305	Tap screw, Phillips PO4IDRIV®: No. 6-32 x 5/16. (Secures A301 & A302).	C522LL C522L	19A700013P9 19A700013P11	Phenolic: 0.47 pf ±5%, 500 VDCw.  Phenolic: 0.68 pf ±5%, 500 VDCw.	12521Tr	19B209420P27	Coil, RF: 15.0 $\mu$ h $\pm 5\%$ , 2.75 ohms DC res max; sim to Jeffers 441316-2J.
R3M*	3R152P243J	Composition: 24K ohms ±5%, 1/4 w. Added by REV C.			·	C522M	19A700013P9	Phenolic: 0.47 pf ±5%, 500 VDCw.	L522L	19B209420P28	Coil, RF: 18.0 $\mu h$ ±5%, 3.00 ohms DC res max; sim to Jeffers 441316-3J.
	3 <b>R</b> 152 <b>P</b> 153J	Composition: 15K ohms ±5%, 1/4 w. Deleted by REV B.			MIF ASSEMBLY 19C320094G1 25-30 MHz (LLL)	С522Н	19A700013P11	Phenolic: 0.68 pf ±5%, 500 VDCW.	L522M	19B209420P27	Coil, RF: 15.0 µh ±5%, 2.75 ohms DC res max; sim to Jeffers 441316-2J.
					19C320094G2 30-36 MHz (L) 19C320094G3 36-42 MHz (M) 19C320094G4 42-50 MHz (H)				1522н	19B209420P28	Coil, RF: 18.0 µh ±5%, 3.00 ohms DC res max;
					13032003401 42-30 mile (11)			·			sim to Jeffers 441316-3J.
RЗН	3R152P622J	Composition: 6.2K ohms ±5%, 1/4 w.				C523	_	(Part of 4502).			
					CAPACITORS	C524	19A116080P3	Polyester: 0.022 µf ±20%, 50 VDCW.			
Wl	5491689P85	Cable, RF: approx 4 inches long. (Includes Pl).	C502LL	5490446Pl	Variable, ceramic: approx 8-50 pf, 350 VDCW, temp coef -750 PPM; sim to Erie Style 557-36.	thru C527			Q501	19All6154Pl	N Type, field effect.
	-		C502L	5490446Pl	Variable, ceramic: approx 8-50 pf, 350 YDCW, temp coef -750 PPM; sim to Erie Style 557-36.	С52811	5490008P139	Silver mica: 330 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.	Q502	19A116818P1	N Channel, field effect.
C301		(Part of L301).	C502M	19A700012P2	Variable, ceramic: 2.5-20 pf, 200 VDCW, temp coef	C528L	5490008P40	Silver mica: 360 pf ±5%, 500 VDCw; sim to			
C302		(Part of L302).			-250 to -700 Parts/M/°C; sim to Panasonic ECV- 12W20X32.	C528M	5490008P139	Electro Motive Type DM-15.  Silver mica: 330 pf ±10%, 500 VDCW; sim to	R503	19A700106P67	Composition: 1.5K ohms ±10%, 1/4 w.
C304	19B209488P2	Ceramic, feed-thru: 1000 pf +100 -0%, 500 VDCW; sim to Allen-Bradley Style FA5D.	С502Н	19A700012P2	Variable, ceramic: 2.5-20 pf, 200 VDCW, temp coef -250 to -700 Parts/M/°C; sim to Panasonic ECV-			Electro Motive Type DM-15.	R521LL	3R151P561J	Composition: 560 ohms ±5%, 1/8 w.
C305	19B209488P1	Ceramic, feed-thru: 6.8 pf ±20%, 500 VDCW; sim			12W2OX32.	С528н	5490008P40	Silver mica: 360 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	R521L	3R151P331J	Composition: 330 ohms ±5%, 1/8 w.
	10000010000	to Allen-Bradley Style FA5D.	C203FT	5490008P21	Silver mica: 56 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	C529	19All6655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCw; sim to RMC Type JF Discap.	R521M R521H	3R151P561J 3R151P331J	Composition: 560 ohms ±5%, 1/8 w.  Composition: 330 ohms ±5%, 1/8 w.
C306	19B209488P2	Ceramic, feed-thru: 1000 pf +100 -0%, 500 VDCW; sim to Allen-Bradley Style FA5D.	C503L	5490008P17	Silver mica: 39 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				R522	19A700106P87	Composition: 10K ohms ±10%, 1/4 w.
			C503M	5490008P13	Silver mica: 27 pf ±5%, 500 VDCW; sim to Electro	FL501LL	19B219573G5	Crystal, freq:	R523	19A700106P77	Composition: 3.9K ohms ±5%, 1/4 w.
L301LL	19B219455G1	Coil. Includes:	С503Н	5490008P8	Motive Type DM-15.  Silver mica: 15 pf ±5%, 500 VDCW; sim to Electro	11001111	13321337343	Resonator A: 11204.000 KHz, Resonator B: 11196.000 KHz,	R524	19A700106P47	Composition: 220 ohms ±5%, 1/4 w.
C1*	5494481P13	Capacitor, ceramic disc: 2000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	CSOSIA	3450006F6	Motive Type DM-15.			Resonator A: 11204.000 KHz, Resonator B: 11196.000 KHz.	R525	19A700106P31	Composition: 47 ohms ±5%, 1/4 w.
		In 19D416478G2 of REV B & earlier:	C504	19A116656P22J0	Ceramic disc: 22 pf ±5%, 500 VDCW, temp coef 0 PPM.	FL501L	19B219574G6	Crystal, freq: Resonator A: 9400.000 KHz,			NETWORKS
	5494481P11	Capacitor, ceramic disc: 1000 pf ±20%, 1000 VDCw; sim to RMC Type JF Discap.	C505	5490008P27	Silver mica: 100 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	l		Resonator B: 9396.024 KHz.	4502ևև	19C320141G4	Coil. Includes:
C301	19B209159P4	Capacitor, variable, air: 1.80 to 8.3 pf, 650 v	C506ւււ	19A116656P27K8	Ceramic: 27 pf ±10%, 500 VDCW, temp coef -80 PPM.	FL501M	19B219573G5	Crystal, freq: Resonator A: 11204.000 KHz, Resonator B: 11196.000 KHz,	/son;	5493185P9 19C320141G5	Tuning slug. Coil. Includes:
201	1000000000	peak; sim to EF Johnson 189.	C506L	19A116656P24K8	Ceramic disc: 24 pf ±10%, 500 VDCW, temp coef		100	Resonator A: 11204.000 KHz, Resonator B: 11196.000 KHz.	4502L	5493185P9	Tuning slug.
DS1 L301L	19B209067P1 19B219455G1	Lamp, glow: 0.7 ma; sim to GE NE2ET.  Coil. Includes:	C506M	19A116656P15K8	-80 PPM.  Ceramic disc: 15 pf ±10%, 500 VDCW, temp coef	F1.501H	19B219574G6	Crystal, freq:	∠502M	19C320141G4	Coil. Includes:
C1	5494481P13	Capacitor, ceramic disc: 2000 pf ±20%, 1000 VDCw;			-80 PPM.			Resonator A: 9400.000 KHz, Resonator B: 9396.024 KHz.		5493185P9	Tuning slug.
0207	19B209159P4	sim to RMC Type JF Discap.  Capacitor, variable, air: 1.80 to 8.3 pf, 650 v	C506H	19A116656P12K8	Ceramic disc: 12 pf ±10%, 500 VDCW, temp coef -80 PPM.	FL502LL		(Part of FL50lLL).	Z502H	19C320141G5	Coil. Includes;
C301	1950013974	peak; sim to EF Johnson 189.	C507LL	19A700013P13	Phenolic: 1.0 pf ±5%, 500 VDCW.	FL502L		(Part of FL501L).		5493185P9	Tuning slug.
D\$1	19B209067Pl	Lamp, glow: 0.7 ma; sim to GE NE2ET.	C507L	19A700013P12	Phenolic: 0.82 pf ±5%, 500 VDCW.	FL502M FL502H		(Part of FL501M). (Part of FL501H).			MISCELLANEOUS
			C507M C507H	19A700013P11 19A700013P10	Phenolic: 0.68 pf ±5%, 500 VDCW.  Phenolic: 0.56 pf ±5%, 500 VDCW.					19B219470P2	Shield.
]			550111							19A129424G1	Can. (Quantity 3).
		<b> </b>								4031594P1 4035306P23	Insulator. (Used with C502, C521).  Washer, fiber. (Used with J501).
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	SYMBOL	GE PART NO.	DESCRIPTION
		·	RECEIVER MOD KIT 19A129750G1
	C2301	19A116656P8J0	Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.
	CR2301	19A116925P1	DIODES AND RECTIFIERS Silicon, pin: 35 volt Reverse Breakdown, 400 mw.
	R2301 R2302	19A700106P95	Composition: 22K ohms ±5%, 1/4 w.  Composition: 680 ohms ±10%, 1/4 w.
	W2301	19B219999G2	Cable, RF: approx 1 foot long, includes connector
			DUAL FRONT END MOD KIT 19A129750G2
	C2301*	19A116656P8J0	Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM. Deleted by REV B.
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## PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

1123	V. A V. A V. A	unru	D - Mixer/IF Board 19C320094G1, G2 C - Mixer/IF Board 19C320094G3, G4
			RF Filter Board 19032007361-64 Above revisions incorporated in initial shipment.
RE	V. в		- RF Filter Board 19C320073G2 & G3
			To improve receiver sensitivity. Deleted R3L and R3M.
RE	v. c		- RF Filter Board 19C320073G3
			To prevent oscillation. Added R3M.
RE	V. B		RF Filter Board 19C320073G1, G4 RF Filter Board 19C320073G2
RE	v. D		- RF Filter Board 19C320073G3
			To improve receiver sensitivity. Changed C2, C3 and C4 and L1 thru L4.
REV	7. D		- RF Filter Board 19C320073G2
			To prevent oscillation in pre-selector board. Added R3L
REV	7. А,	В	- RF Assembly 19D416478G1-G4
			Incorporated in initial shipment.
REV	. с		- RF Assembly 19D416478G1
			To improve sensitivity in 25-30 MHz range. Changed Cl (part of L301).
	. C		- RF Filter Board 19C320073G1, G4
			- RF Filter Board 19C320073G2, G3 To standardize components. Deleted Q1 and PWB 19C320072.
			Added Q2 and PWB 19C327760P1.
REV	. F		- RF Filter Board 19C320073G2
			To improve RF sensitivity. Deleted R3L.